

## Features

- ESD Protected Up To 2KV (HBM)
- Trench LV MOSFET Technology
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device <sup>(Note 1)</sup>
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

## Maximum Ratings

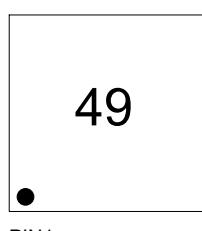
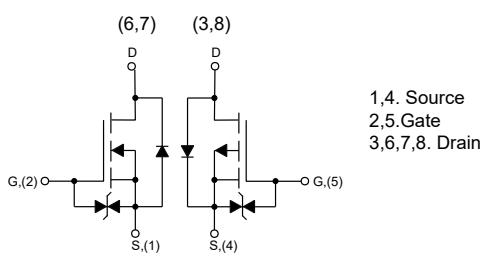
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 360°C/W Junction to Ambient <sup>(Note 2)</sup>

Parameter	Symbol	Rating	Unit
Total Power Dissipation <sup>(Note 4)</sup>	P <sub>D</sub>	0.35	W
<b>N-Channel MOSFET</b>			
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±10	V
Continuous Drain Current	I <sub>D</sub>	0.75 0.47	A
Pulsed Drain Current <sup>(Note 3)</sup>	I <sub>DM</sub>	3	A
<b>P-Channel MOSFET</b>			
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GS</sub>	±10	V
Continuous Drain Current	I <sub>D</sub>	-0.52 -0.33	A
Pulsed Drain Current <sup>(Note 3)</sup>	I <sub>DM</sub>	-2.08	A

Note:

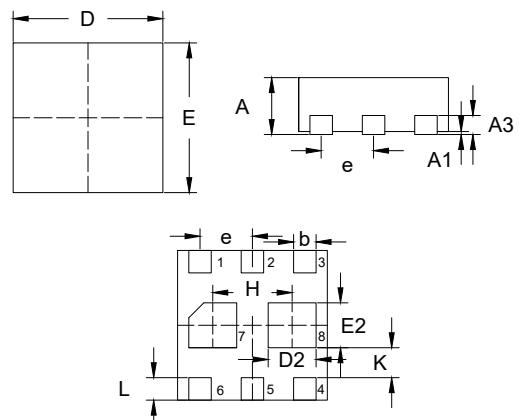
1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of R<sub>θJA</sub> is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P<sub>D</sub> is based on max. junction temperature, using junction-ambient thermal resistance.

## Internal Structure and Marking Code



## Dual N&P-Channel MOSFET

DFN1010B-6



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.012	0.016	0.31	0.40	
A1	0.000	0.002	0.00	0.05	
A3	0.005		0.127		TYP.
b	0.004	0.008	0.10	0.20	
D	0.037	0.041	0.95	1.05	
E	0.037	0.041	0.95	1.05	
e	0.014		0.350		TYP.
D2	0.011	0.015	0.27	0.37	
E2	0.010	0.014	0.25	0.35	
H	0.021		0.530		TYP.
L	0.004	0.008	0.10	0.20	
K	0.008	-	0.20	-	

**N-Channel ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	20			V
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.35	0.7	1.2	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1.0	μA
Gate-body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V			±10	μA
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =0.5A		173	250	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =0.4A		250	340	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =0.2A		405	950	
Gate Resistance	R <sub>g</sub>	f=1 MHz, Open drain		44		Ω
<b>Diode Characteristics</b>						
Continuous Body Diode Current	I <sub>S</sub>				0.75	A
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =0.5A			1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =0.1A, dI <sub>F</sub> /dt=100A/μs		5.5		ns
Reverse Recovery Charge	Q <sub>rr</sub>			0.8		nC
<b>Dynamic Characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =16V, V <sub>GS</sub> =0V, f=1MHz		33		pF
Output Capacitance	C <sub>oss</sub>			10		
Reverse Transfer Capacitance	C <sub>rss</sub>			5.6		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =0.1A		1.2		nC
Gate-Source Charge	Q <sub>gs</sub>			0.2		
Gate-Drain Charge	Q <sub>gd</sub>			0.2		
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V, V <sub>GS</sub> =4.5V I <sub>D</sub> =0.5A, R <sub>G</sub> =10Ω		5.4		ns
Turn-on Rise Time	t <sub>r</sub>			5.2		
Turn-off Delay Time	t <sub>d(off)</sub>			10.5		
Turn-off Fall Time	t <sub>f</sub>			5.7		

**P-Channel ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-20			V
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±10V			± 10	μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -20V, V <sub>GS</sub> =0V			-1	μA
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.35	-0.62	-1.2	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-0.5A		580	850	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-0.3A		855	1200	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-0.2A		1350	2000	
Gate Resistance	R <sub>g</sub>	f=1 MHz, Open drain		85		Ω
<b>Diode Characteristics</b>						
Continuous Body Diode Current	I <sub>S</sub>				-0.65	A
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-0.5A			-1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =-1A, dI <sub>F</sub> /dt=20A/μs		32		ns
Reverse Recovery Charge	Q <sub>rr</sub>			3.1		nC
<b>Dynamic Characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10V, V <sub>GS</sub> =0V, f=1MHz		36		pF
Output Capacitance	C <sub>oss</sub>			12		
Reverse Transfer Capacitance	C <sub>rss</sub>			6.4		
Total Gate Charge	Q <sub>g</sub>	V <sub>DD</sub> = -10V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1A		1.4		nC
Gate-Source Charge	Q <sub>gs</sub>			0.4		
Gate-Drain Charge	Q <sub>gd</sub>			0.3		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-10V, V <sub>GS</sub> =-4.5V, R <sub>G</sub> =3Ω, I <sub>D</sub> =-0.5A		3.2		ns
Turn-On Rise Time	t <sub>r</sub>			18.6		
Turn-Off Delay Time	t <sub>d(off)</sub>			8.3		
Turn-Off Fall Time	t <sub>f</sub>			21.4		

## Curve Characteristics (N-Channel)

Fig. 1 - Typical Output Characteristics

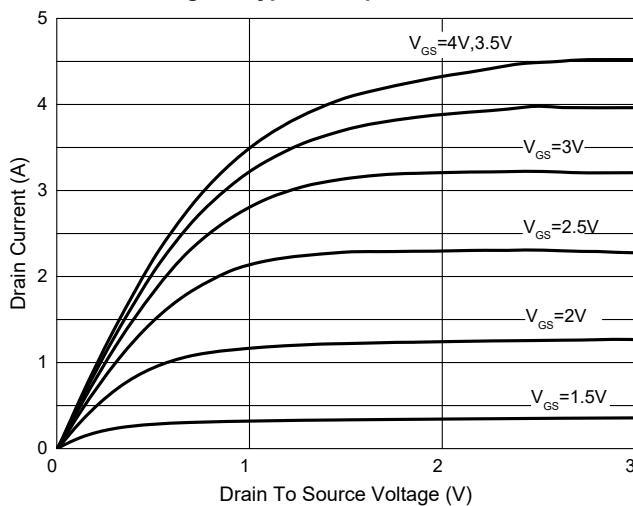


Fig. 2 - Transfer Characteristics

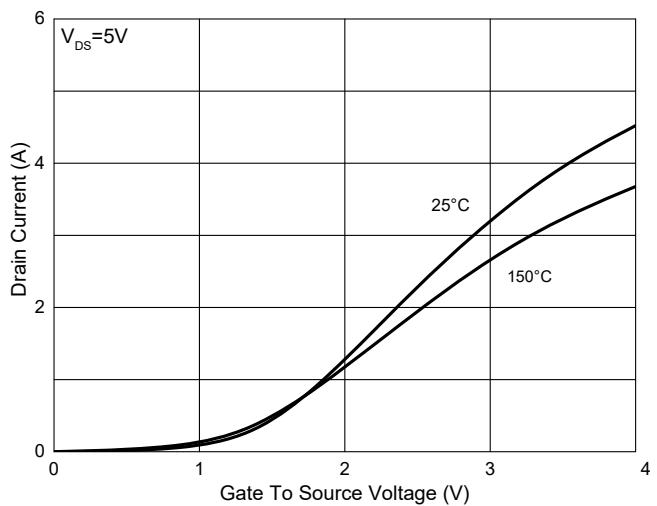


Fig. 3 -  $R_{DS(ON)}$ — $V_{GS}$

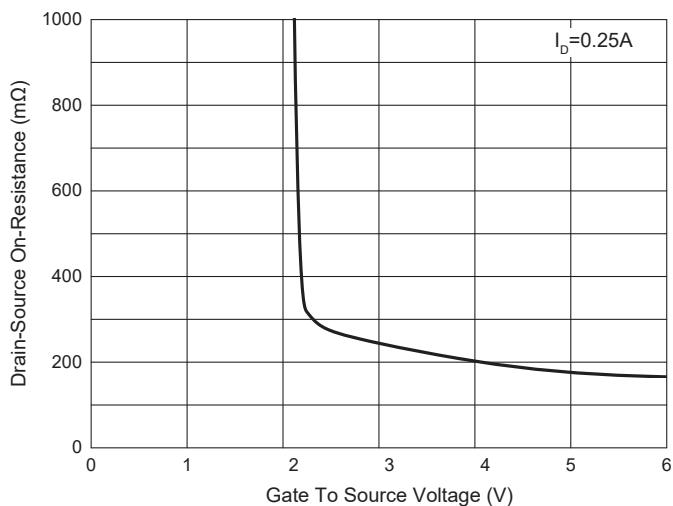


Fig. 4 -  $R_{DS(ON)}$ — $I_D$

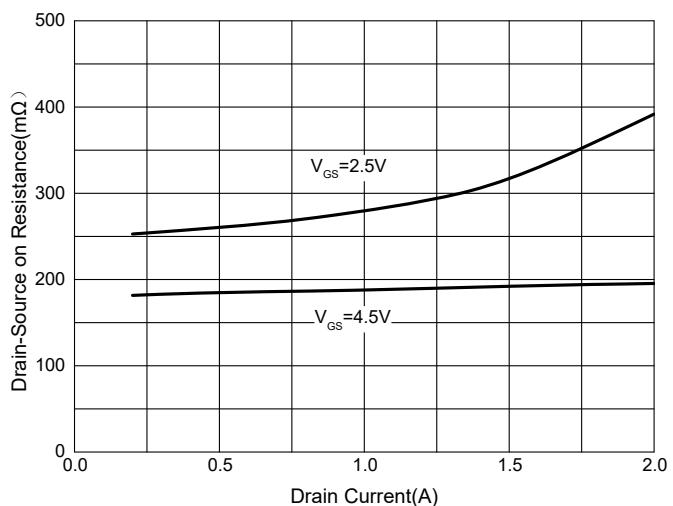


Fig. 5 - Capacitance Characteristics

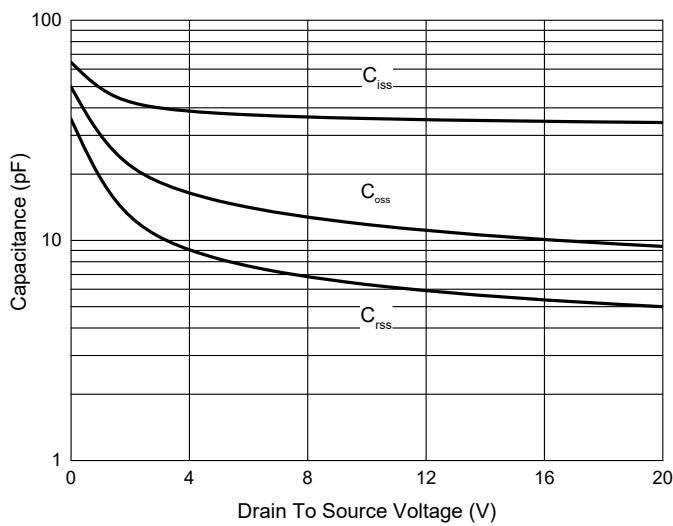
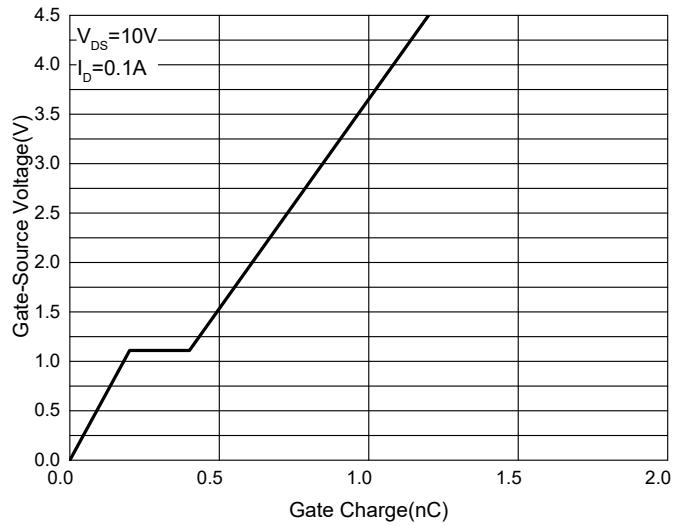


Fig. 6 - Gate Charge



## Curve Characteristics (N-Channel)

Fig. 7 - Normalized Threshold Voltage

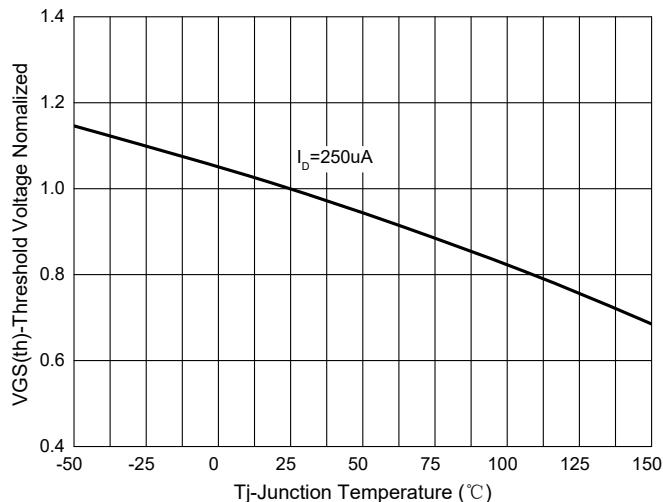


Fig.8-Normalized On Resistance Characteristics

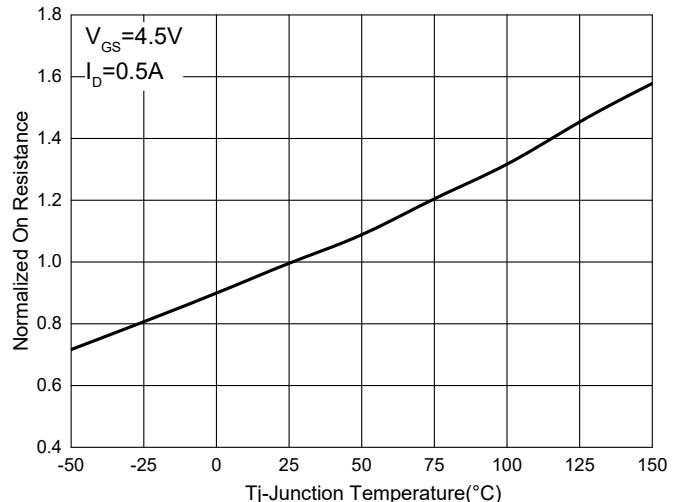


Fig.9 -  $I_s - V_{SD}$

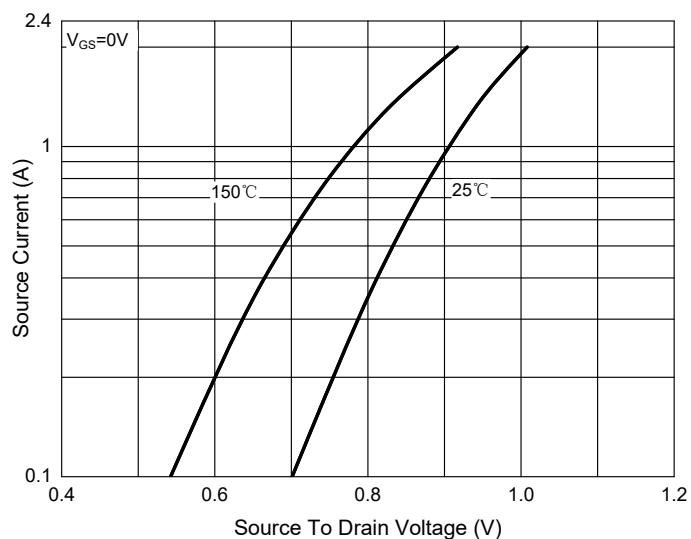


Fig. 10 - Drain Current

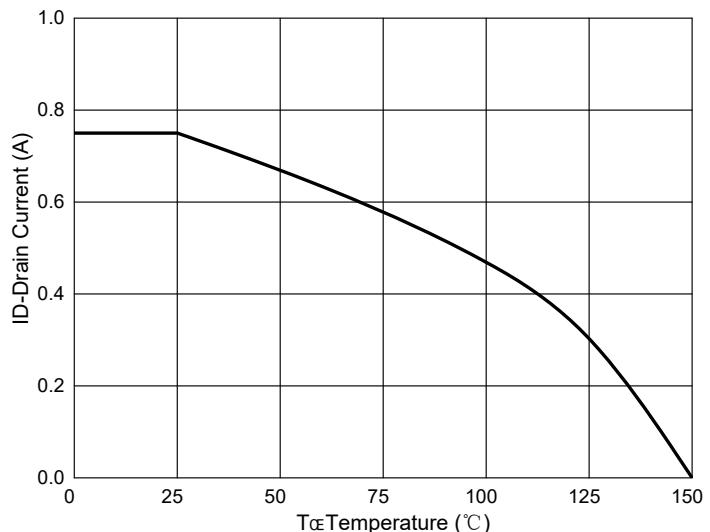
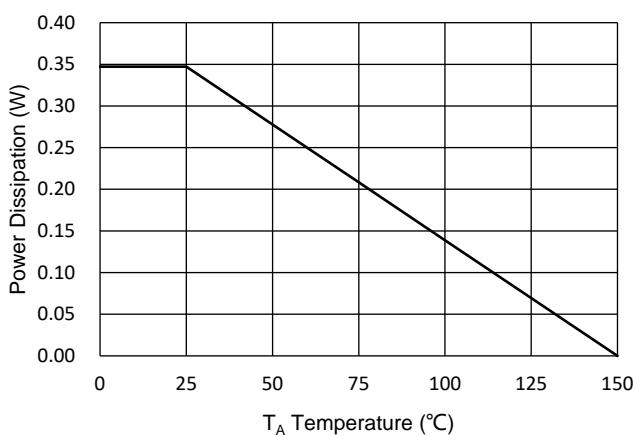


Fig.11 - PD Dissipation



## Curve Characteristics (N-Channel)

Fig. 12 - Safe Operation Area

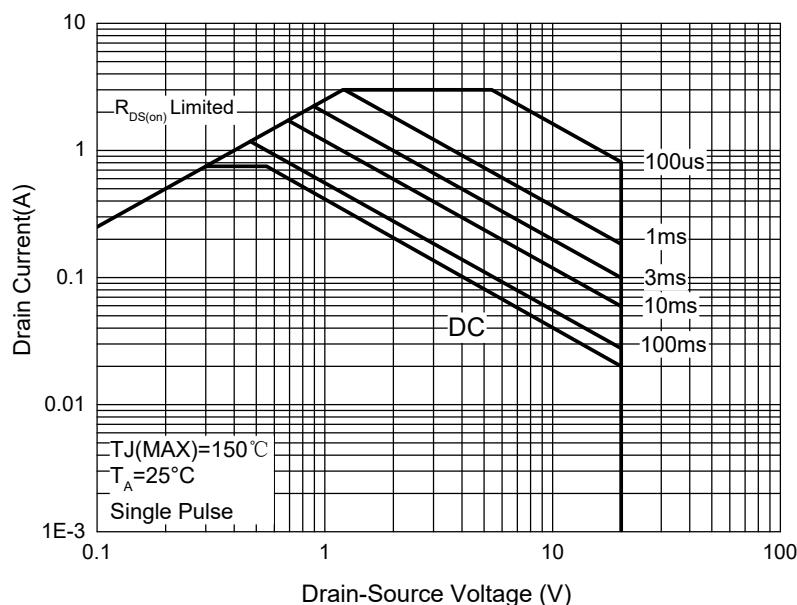
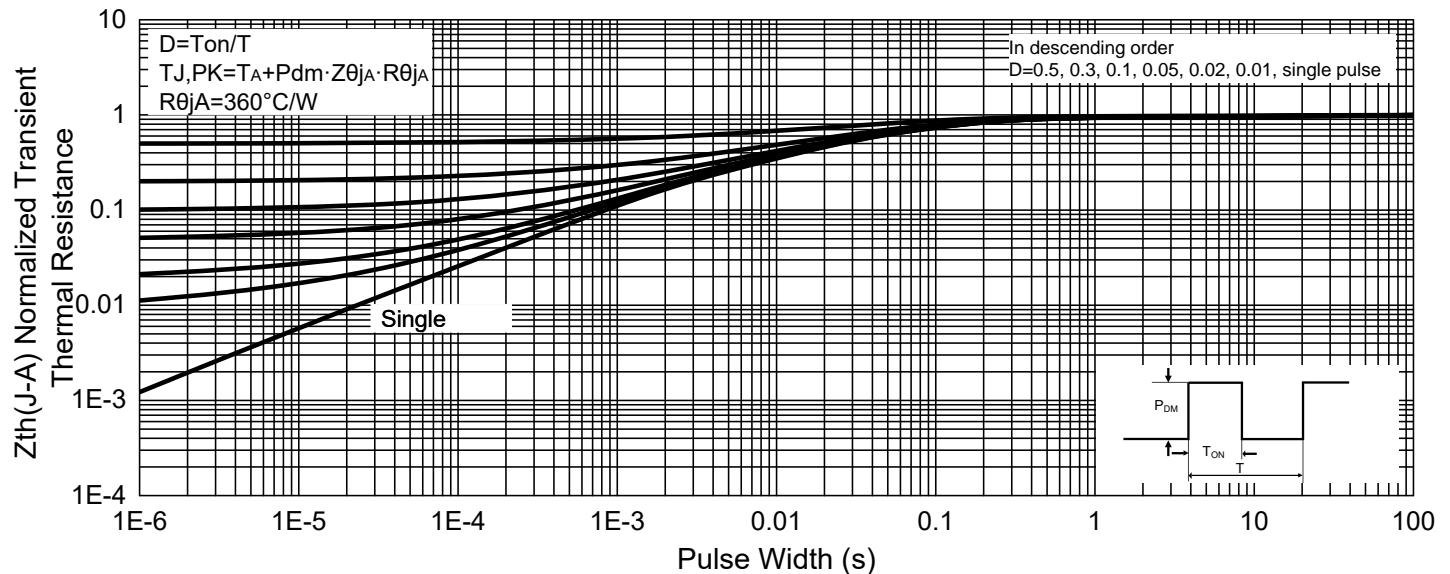


Fig. 13 - Normalized Transient Thermal Impedance



## Curve Characteristics (P-Channel)

Fig. 1 - Typical Output Characteristics

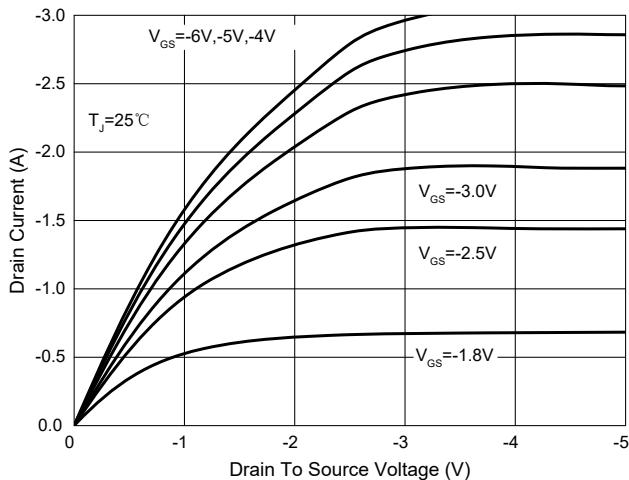


Fig. 2 - Transfer Characteristics

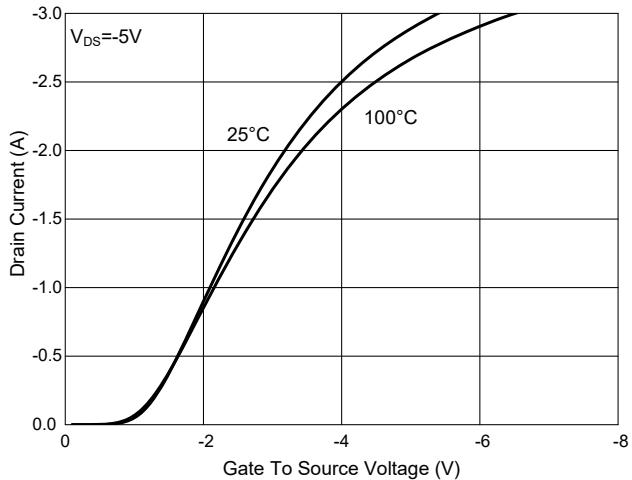


Fig. 3 -  $R_{DS(ON)}$  —  $V_{GS}$

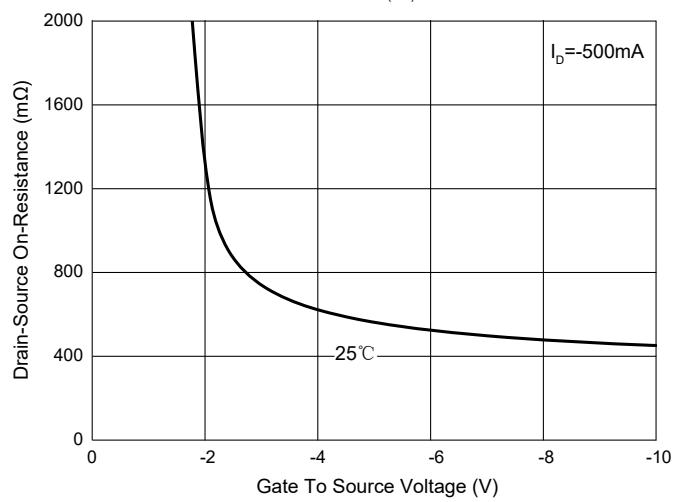


Fig. 4 -  $R_{DS(ON)}$  —  $I_D$

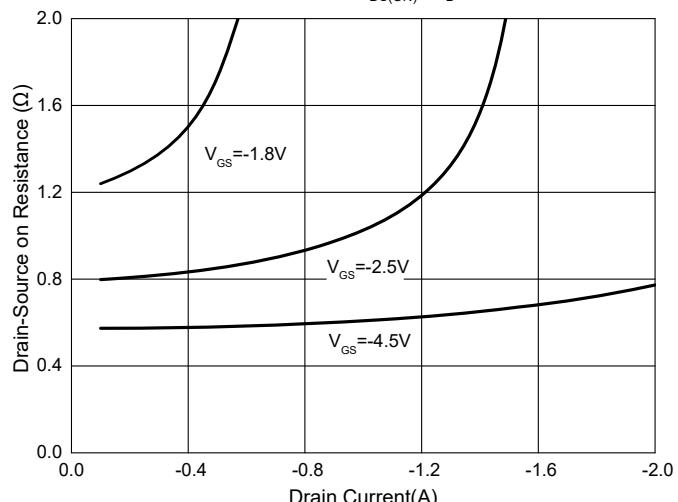


Fig. 5 - Capacitance Characteristics

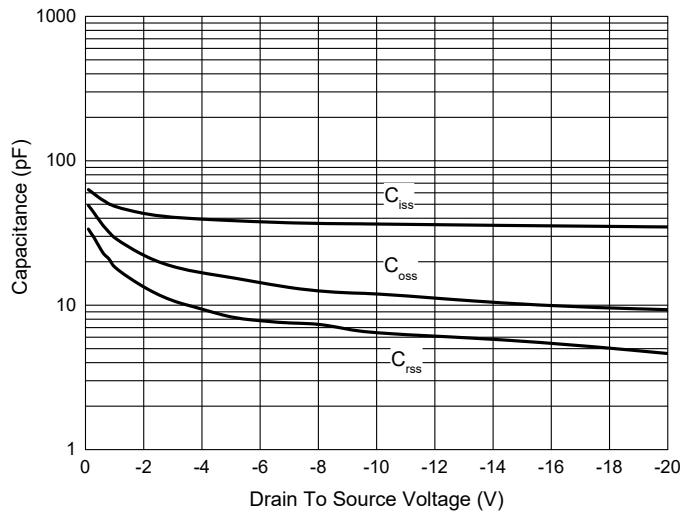
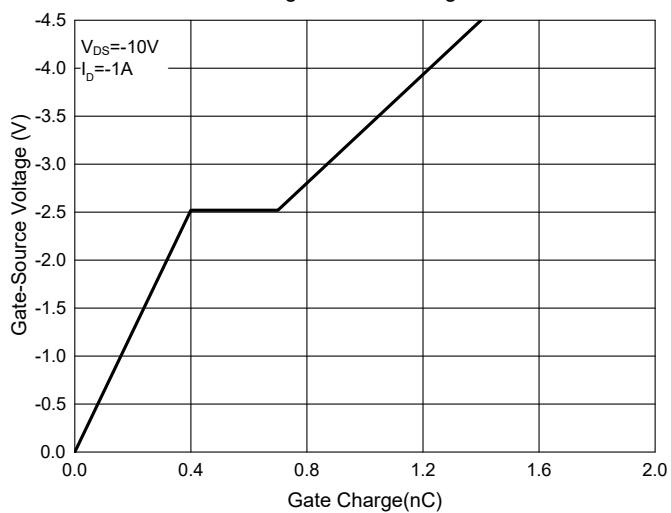


Fig. 6 - Gate Charge



## Curve Characteristics (P-Channel)

Fig. 7 - Normalized Threshold voltage

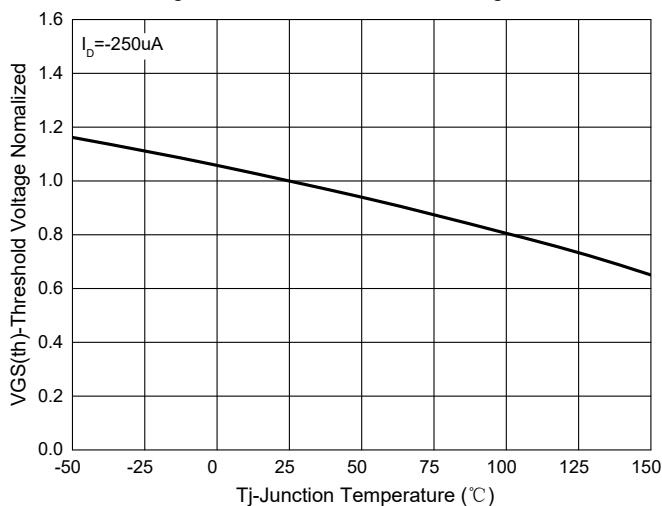


Fig. 8 - Normalized On Resistance Characteristics

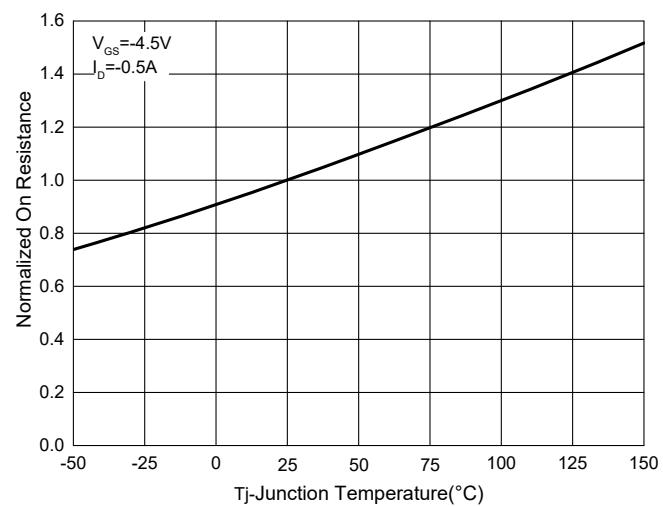


Fig. 9 -  $I_s$ — $V_{SD}$

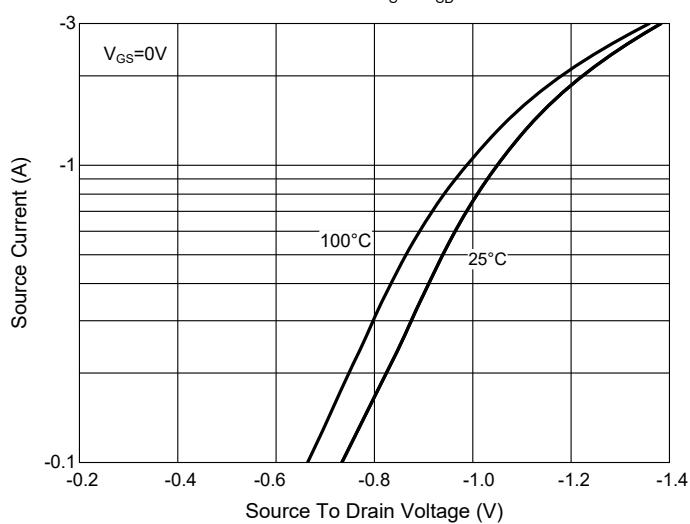


Fig.10 - Drain Current

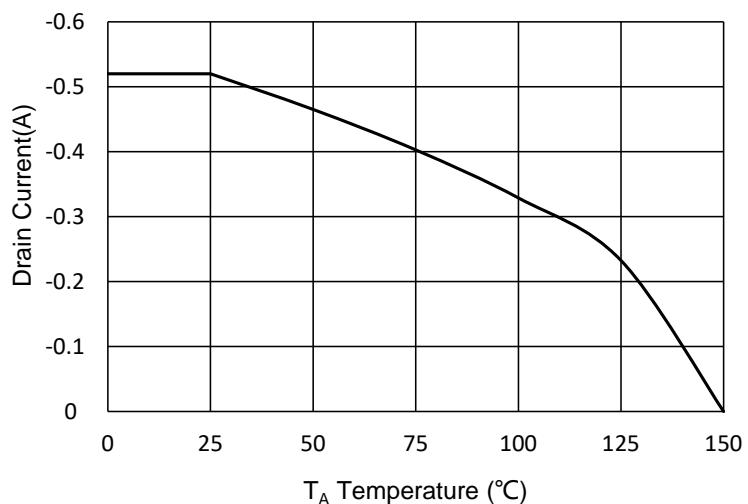
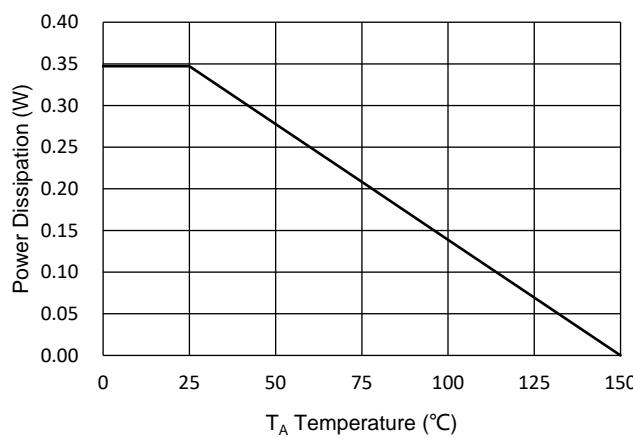


Fig.11 - PD Dissipation



## Curve Characteristics (P-Channel)

Fig.12 - Safe Operation Area

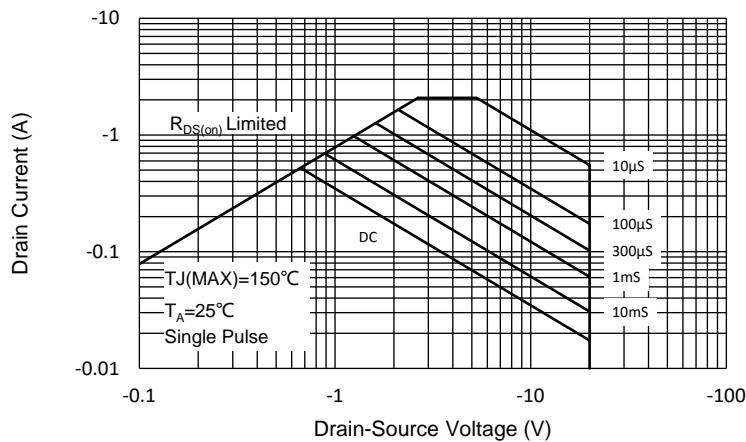
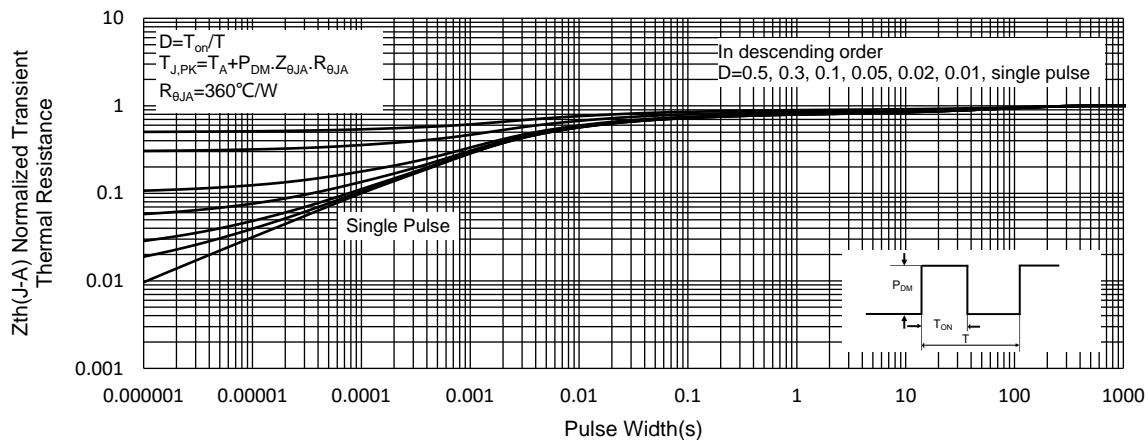


Fig.13 - Normalized Transient Thermal Impedance



## Ordering Information

Device	Packing
Part Number-TP	Tape&Reel:5Kpcs/Reel

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